



INFORMATION DISCLOSURE STATEMENT

Applicant : Brabant et al.
App. No : 10/800,390
Filed : 12 March 2004
For : EPITAXIAL SEMICONDUCTOR DEPOSITION
METHODS AND STRUCTURES
Examiner : David Vu
Art Unit : 2818

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

Enclosed for filing in the above-identified application is a PTO/SB/08 Equivalent listing 41 references to be considered by the Examiner. Also enclosed are 30 foreign patent references and/or non-patent literature as listed on the Information Disclosure Statement.

This Information Disclosure Statement is being filed before the mailing date of a final action and before the mailing of a Notice of Allowance. This Statement is accompanied by the fees set forth in 37 C.F.R. § 1.17(p). The Commissioner is hereby authorized to charge any additional fees which may be required or to credit any overpayment to Account No. 11-1410.

Respectfully submitted,
KNOBBE, MARTENS, OLSON & BEAR, LLP

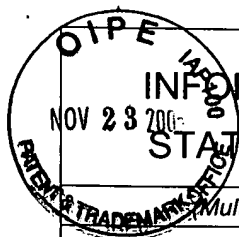
Dated: 21 nov 05

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Multiple sheets used when necessary)

SHEET 1 OF 4

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| Examiner | David Vu |
| Attorney Docket No. | ASMEX.448A |

U.S. PATENT DOCUMENTS

| Examiner Initials | Cite No. | Document Number Number - Kind Code (if known) Example: 1,234,567 B1 | Publication Date MM-DD-YYYY | Name of Patentee or Applicant | Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear |
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| | 11 | 2004/0219735 | 11/04/04 | Brabant et al. | |

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|-------------------|----------|--|--------------------------------|-------------------------------|--|----------------|
| | 12 | WO 01/41544 | 06/14/01 | PCT | | |

NON PATENT LITERATURE DOCUMENTS

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